

# SN74CBTLV16211 LOW-VOLTAGE 24-BIT FET BUS SWITCH

SCDS043E – DECEMBER 1997 – REVISED APRIL 1999

- **5-Ω Switch Connection Between Two Ports**
- **Isolation Under Power-Off Conditions**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic Thin Shrink Small-Outline (DGG), Thin Very Small-Outline (DGV), and 300-mil Shrink Small-Outline (DL) Packages**

## description

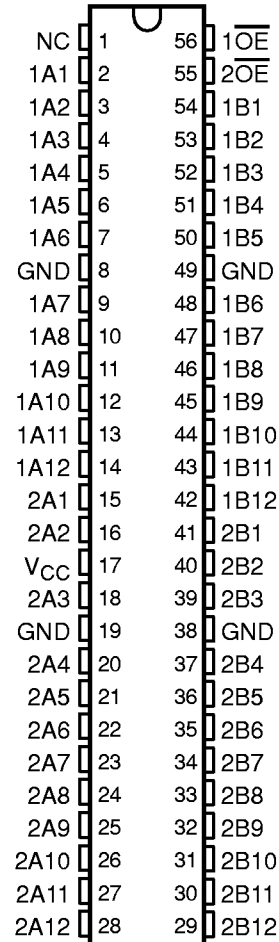
The SN74CBTLV16211 provides 24 bits of high-speed bus switching. The low on-state resistance of the switch allows connections to be made with minimal propagation delay.

The device is organized as dual 12-bit bus switches with separate output-enable ( $\overline{OE}$ ) inputs. It can be used as two 12-bit bus switches or one 24-bit bus switch. When  $\overline{OE}$  is low, the associated 12-bit bus switch is on and port A is connected to port B. When  $\overline{OE}$  is high, the switch is open, and the high-impedance state exists between the two ports.

To ensure the high-impedance state during power up or power down,  $\overline{OE}$  should be tied to  $V_{CC}$  through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74CBTLV16211 is characterized for operation from  $-40^{\circ}\text{C}$  to  $85^{\circ}\text{C}$ .

**DGG, DGV, OR DL PACKAGE  
(TOP VIEW)**



NC – No internal connection

**FUNCTION TABLE  
(each 12-bit bus switch)**

INPUT $\overline{OE}$	FUNCTION
L	A port = B port
H	Disconnect



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## recommended operating conditions (see Note 3)

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage		2.3	3.6	V
V <sub>IH</sub>	High-level control input voltage	V <sub>CC</sub> = 2.3 V to 2.7 V	1.7		V
		V <sub>CC</sub> = 2.7 V to 3.6 V	2		
V <sub>IL</sub>	Low-level control input voltage	V <sub>CC</sub> = 2.3 V to 2.7 V		0.7	V
		V <sub>CC</sub> = 2.7 V to 3.6 V		0.8	
T <sub>A</sub>	Operating free-air temperature		-40	85	°C

NOTE 3: All unused control inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

## electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP†	MAX	UNIT
V <sub>IK</sub>		V <sub>CC</sub> = 3 V,	I <sub>I</sub> = -18 mA			-1.2	V
I <sub>I</sub>		V <sub>CC</sub> = 3.6 V,	V <sub>I</sub> = V <sub>CC</sub> or GND			±1	μA
I <sub>off</sub>		V <sub>CC</sub> = 0,	V <sub>I</sub> or V <sub>O</sub> = 0 to 3.6 V			10	μA
I <sub>CC</sub>		V <sub>CC</sub> = 3.6 V,	I <sub>O</sub> = 0, V <sub>I</sub> = V <sub>CC</sub> or GND			10	μA
ΔI <sub>CC</sub> ‡	Control inputs	V <sub>CC</sub> = 3.6 V,	One input at 3 V, Other inputs at V <sub>CC</sub> or GND			300	μA
C <sub>i</sub>	Control inputs	V <sub>I</sub> = 3.3 V or 0				4.5	pF
C <sub>iO(OFF)</sub>		V <sub>O</sub> = 3.3 V or 0,	$\overline{\text{OE}} = V_{CC}$			6.5	pF
r <sub>on</sub> §	V <sub>CC</sub> = 2.3 V, TYP at V <sub>CC</sub> = 2.5 V	V <sub>I</sub> = 0	I <sub>I</sub> = 64 mA		5	8	Ω
			I <sub>I</sub> = 24 mA		5	8	
		V <sub>I</sub> = 1.7 V,	I <sub>I</sub> = 15 mA		27	40	
	V <sub>CC</sub> = 3 V	V <sub>I</sub> = 0	I <sub>I</sub> = 64 mA		5	7	
			I <sub>I</sub> = 24 mA		5	7	
		V <sub>I</sub> = 2.4 V,	I <sub>I</sub> = 15 mA		10	15	

† All typical values are at V<sub>CC</sub> = 3.3 V (unless otherwise noted), T<sub>A</sub> = 25°C.

‡ This is the increase in supply current for each input that is at the specified voltage level rather than V<sub>CC</sub> or GND.

§ Measured by the voltage drop between the A and B terminals at the indicated current through the switch. On-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

## switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = 2.5 V ± 0.2 V		V <sub>CC</sub> = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	
t <sub>pd</sub> ¶	A or B	B or A	0.15		0.25		ns
t <sub>en</sub>	$\overline{\text{OE}}$	A or B	1	7	1	6.2	ns
t <sub>dis</sub>	$\overline{\text{OE}}$	A or B	1	7.2	1	7.7	ns

¶ The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

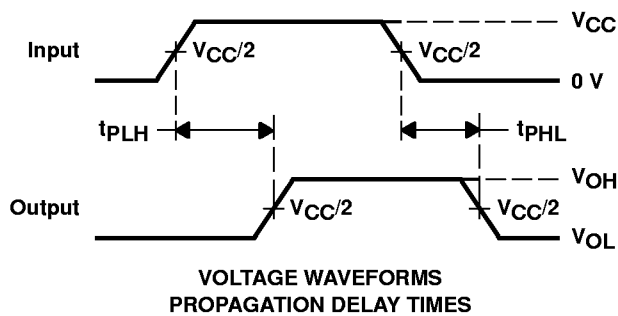
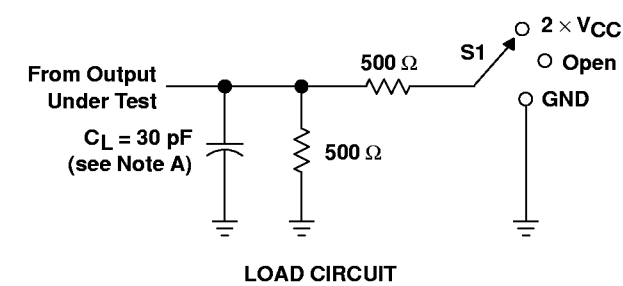


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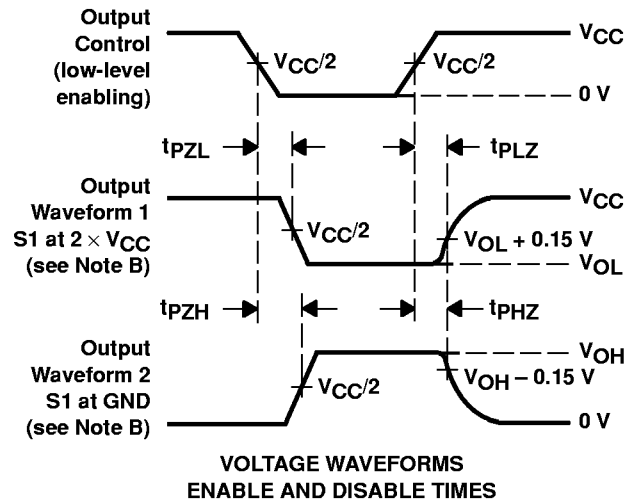
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## PARAMETER MEASUREMENT INFORMATION

$$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$$



TEST	S1
$t_{pd}$	Open
$t_{PLZ}/t_{PZL}$	2 $\times$ $V_{CC}$
$t_{PHZ}/t_{PZH}$	GND

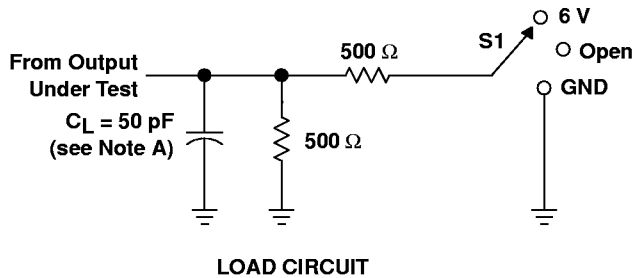


- NOTES:
- A.  $C_L$  includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics:  $PRR \leq 10 \text{ MHz}$ ,  $Z_O = 50 \Omega$ ,  $t_r \leq 2 \text{ ns}$ ,  $t_f \leq 2 \text{ ns}$ .
  - D. The outputs are measured one at a time with one transition per measurement.
  - E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
  - F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
  - G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .

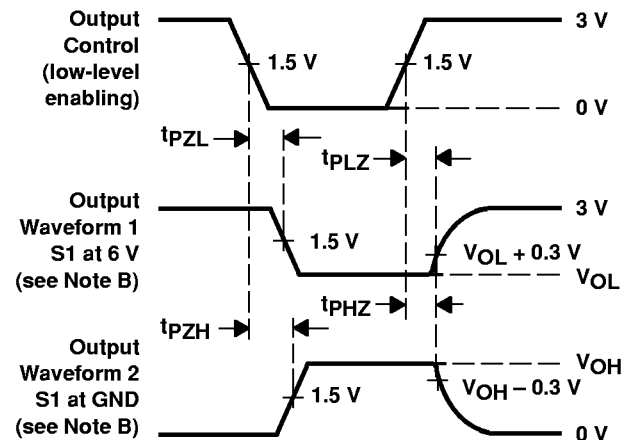
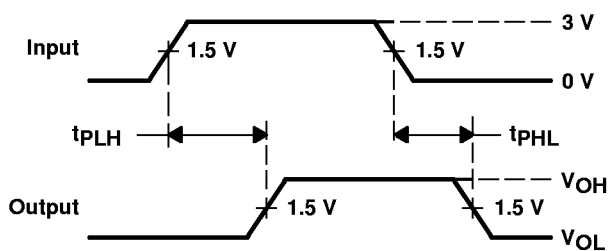
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION

$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$



TEST	S1
$t_{pd}$	Open
$t_{PLZ}/t_{PZL}$	6 V
$t_{PHZ}/t_{PZH}$	GND



- NOTES:
- $C_L$  includes probe and jig capacitance.
  - Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
  - All input pulses are supplied by generators having the following characteristics:  $PRR \leq 10 \text{ MHz}$ ,  $Z_O = 50 \Omega$ ,  $t_r \leq 2.5 \text{ ns}$ ,  $t_f \leq 2.5 \text{ ns}$ .
  - The outputs are measured one at a time with one transition per measurement.
  - $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
  - $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
  - $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .

Figure 2. Load Circuit and Voltage Waveforms

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